

Title (en)

PIEZOELECTRIC RESONATOR AND PIEZOELECTRIC FILTER

Title (de)

PIEZOELEKTRISCHER RESONATOR UND PIEZOELEKTRISCHES FILTER

Title (fr)

RESONATEUR PIEZOELECTRIQUE ET FILTRE PIEZOELECTRIQUE

Publication

EP 2003775 A9 20090506 (EN)

Application

EP 07740050 A 20070328

Priority

- JP 2007056612 W 20070328
- JP 2006104195 A 20060405

Abstract (en)

[origin: EP2003775A2] A piezoelectric resonator is obtained that is capable of having a reduced size and thickness thereof and that is less prone to having a spurious component occurring in a mode at which it propagates in a piezoelectric thin film at a range higher than a resonant frequency. A piezoelectric resonator includes a laminated thin film having a first thin film portion supported by a substrate 2 and a second thin film portion separated from a first main surface of the substrate and acoustically isolated. The second thin film portion of the laminated thin film includes a piezoelectric thin film 5, a first electrode 12 disposed on the upper surface of the piezoelectric thin film, and a second electrode 13 disposed on the lower surface of the piezoelectric thin film and being larger and thicker than the first electrode. The piezoelectric resonator further includes a mass adding film 11 disposed around the first electrode 12 and on at least one part of a region outside the periphery of a piezoelectric vibrating portion where the first and second electrodes 12 and 13 overlap each other with the piezoelectric thin film 5 disposed therebetween. The second electrode 13 is formed, in plan view, so as to extend beyond the piezoelectric vibrating portion to a region at which the mass adding film 11 is disposed.

IPC 8 full level

H03H 9/17 (2006.01); **H10N 30/00** (2023.01); **H10N 30/87** (2023.01); **H03H 9/54** (2006.01); **H03H 9/58** (2006.01); **H10N 30/01** (2023.01); **H10N 30/06** (2023.01); **H10N 30/093** (2023.01); **H10N 30/20** (2023.01); **H10N 30/85** (2023.01)

CPC (source: EP US)

H03H 3/04 (2013.01 - EP US); **H03H 9/02118** (2013.01 - EP US); **H03H 9/173** (2013.01 - EP US); **H03H 9/564** (2013.01 - EP US); **H03H 2003/0428** (2013.01 - EP US); **H03H 2003/0442** (2013.01 - EP US); **H03H 2003/0471** (2013.01 - EP US)

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC MT NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

EP 2003775 A2 20081217; **EP 2003775 A4 20110427**; **EP 2003775 A9 20090506**; JP 4661958 B2 20110330; JP WO2007119556 A1 20090827; US 2009001848 A1 20090101; US 7649304 B2 20100119; WO 2007119556 A1 20071025

DOCDB simple family (application)

EP 07740050 A 20070328; JP 2007056612 W 20070328; JP 2008510873 A 20070328; US 21186508 A 20080917